SMD Schottky Barrier Diode

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CDBU0230 (Lead-free Device)

Io = 200 mA
VR = 30 Volts

Features

Designed for mounting on small surface.

Extremely thin/leadless package.

Low drop-down voltage.

Majority carrier conduction.

Mechanical data

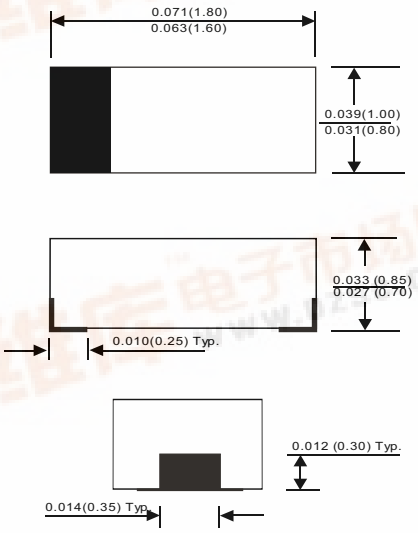
Case: 0603 (1608) Standard package , molded plastic.

Terminals: Gold plated, solderable per MIL-STD-750, method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any.

Weight: 0.003 gram (approximately).



Dimensions in inches and (millimeter)

Maximum Rating (at TA = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		VRRM			35	V
Reverse voltage		VR			30	V
Average forward current		Io			200	mA
Forward current , surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	IFSM		2000		mA
Power Dissipation		PD			150	mW
Storage temperature		TSTG	-40		+125	°C
Junction temperature		Tj	-40		+125	°C

Electrical Characteristics (at TA = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	IF = 200 mA DC	VF			0.50	V
Reverse current	VR = 30 V	IR			30	uA
Capacitance between terminals	f = 1MHz, and 10 VDC reverse voltage	CT		9		pF

RATING AND CHARACTERISTIC CURVES (CDBU0230)

Fig. 1 - Forward characteristics

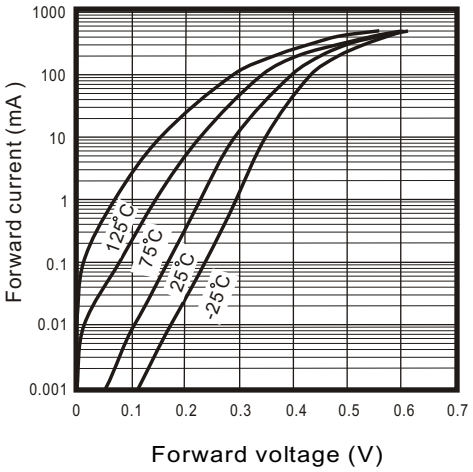


Fig. 2 - Reverse characteristics

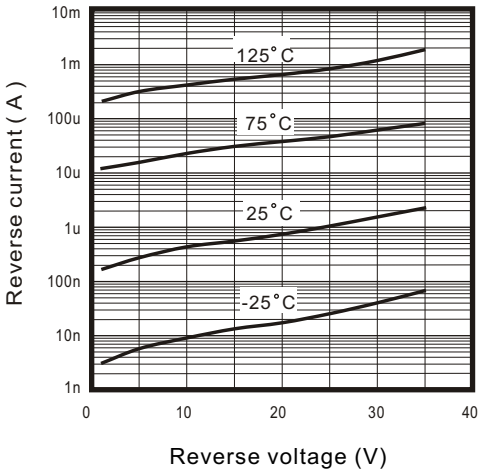


Fig. 3 - Capacitance between terminals characteristics

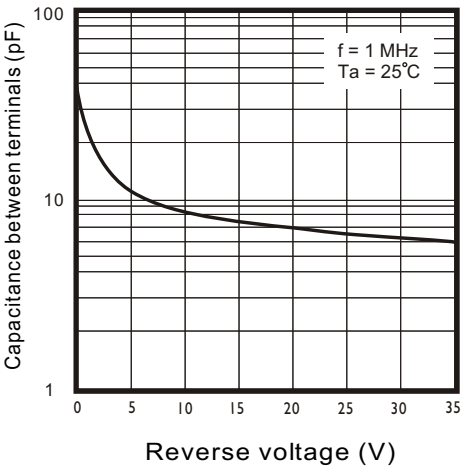


Fig. 4 - Current derating curve